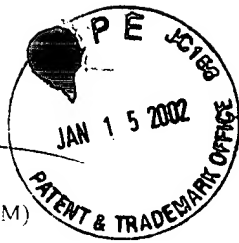


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December 27, 2001 (9:33AM)



Docket: AM-3245

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Date: Dec 27, 2001 Ingrid C. Mallory  
Ingrid C. Mallory

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**In re Application of:** Hoiman HUNG et al.

**Attorneys Docket:** AM-3245

**Serial No.:** 09/276,376

**Art Unit No.:** 1746

**Filed:** March 25, 1999

**Examiner:** A. Olsen

**For:** "ENHANCEMENT OF SILICON OXIDE ETCH RATE AND SUBSTRATE SELECTIVITY WITH XENON ADDITION"

Commissioner of Patents and Trademarks  
Washington, DC 20231

**AMENDMENT UNDER 37 CFR §1.111**

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Sir:

In response to the Office Action of September 10, 2001, please amend the above application as follows:

**In the specification:**

**Paragraph at page 5, lines 2-16:**

el  
An example of an inductively coupled plasma etch reactor is the Inductive Plasma Source (IPS) etch reactor, which is available from Applied Materials and which Collins et al. describe in U.S. Patent Application, Serial No. 08/733,544, filed October 21, 1996 and in European Patent Publication EP-840,365-A2. As shown in FIG. 3, a wafer 30 to be processed is closely supported

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